2SK1836, 2SK1837

Silicon N-Channel MOS FET

HITACHI

ADE-208-1326 (Z)
1st. Edition
Mar. 2001

Application

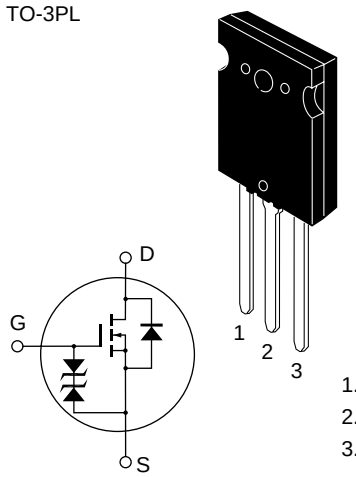
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switchingregulator, DC-DC converter

Outline

TO-3PL



1. Gate
2. Drain (Flange)
3. Source

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	K1836	V_{DSS}	450	V
	K1837		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	50	A
Drain peak current		$I_{D(pulse)}$*[1]	200	A
Body to drain diode reverse drain current		I_{DR}	50	A
Channel dissipation		Pch*[2]	250	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	–55 to +150	°C

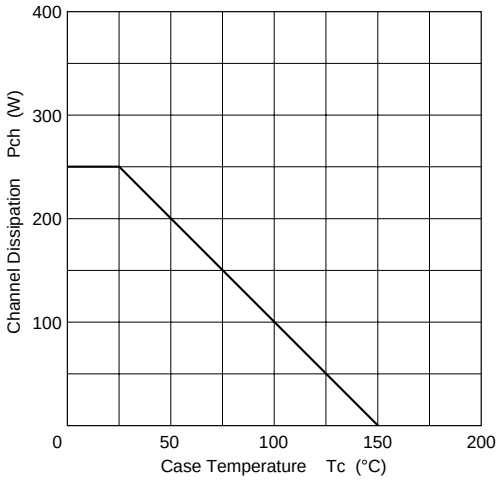
Notes 1. PW ≤ 10 µs, duty cycle ≤ 1 %
2. Value at Tc = 25 °C

Electrical Characteristics (Ta = 25°C)

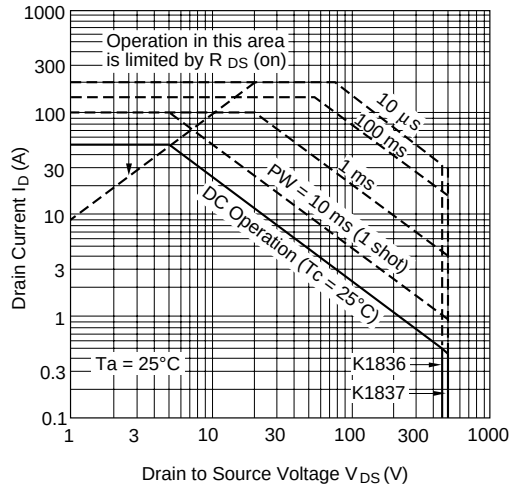
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	K1836	$V_{(BR)DSS}$	450	—	—	V	I_D = 10 mA, V_{GS} = 0
	K1837		500	—	—		
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current		I_{GSS}	—	—	±10	µA	V_{GS} = ±25 V, V_{DS} = 0
Zero gate voltage drain current	K1836	I_{DSS}	—	—	250	µA	V_{DS} = 360 V, V_{GS} = 0
	K1837						V_{DS} = 400 V, V_{GS} = 0
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	I_D = 1 mA, V_{DS} = 10 V
Static drain to source on state resistance	K1836	$R_{DS(on)}$	—	0.08	0.10	Ω	I_D = 25 A
	K1837		—	0.085	0.11		V_{GS}= 10 V*[1]
Forward transfer admittance		$\|y_{fs}\|$	22	35	—	S	I_D = 25 A V_{DS} = 10 V*[1]
Input capacitance		Ciss	—	8150	—	pF	V_{DS} = 10 V
Output capacitance		Coss	—	2100	—	pF	V_{GS} = 0
Reverse transfer capacitance		Crss	—	180	—	pF	f = 1 MHz
Turn-on delay time		$t_{d(on)}$	—	80	—	ns	I_D = 25 A
Rise time		t_r	—	250	—	ns	V_{GS} = 10 V
Turn-off delay time		$t_{d(off)}$	—	550	—	ns	R_L = 1.2 Ω
Fall time		t_f	—	220	—	ns	
Body to drain diode forward voltage		V_{DF}	—	1.1	—	V	I_F = 50 A, V_{GS} = 0
Body to drain diode reverse recovery time		t_{rr}	—	620	—	ns	I_F = 50 A, V_{GS} = 0, di_F / dt = 100 A / µs

Note 1. Pulse Test

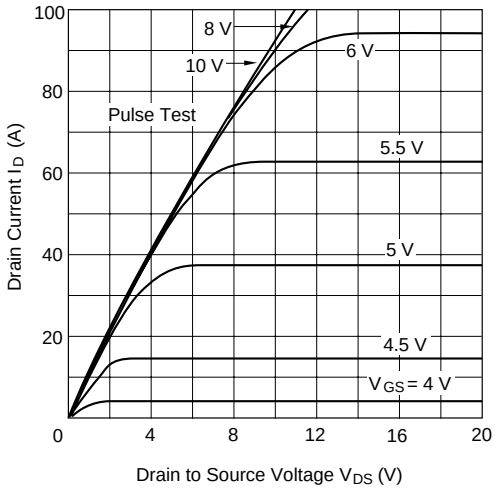
Power vs. Temperature



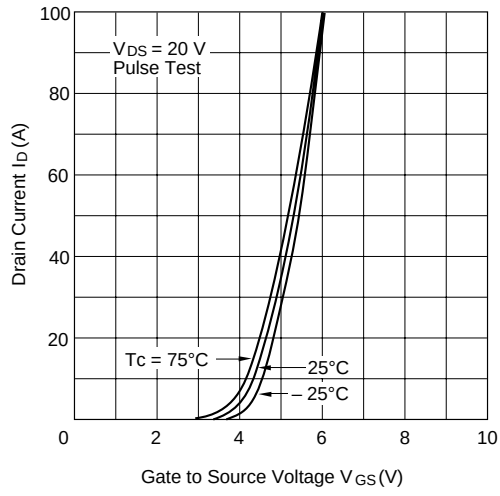
Maximum Safe Operation Area



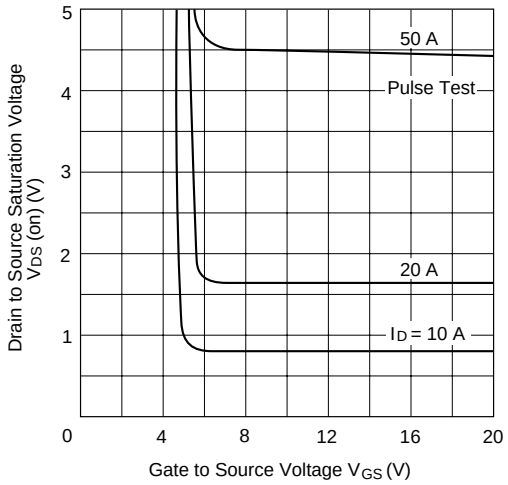
Typical Output Characteristics



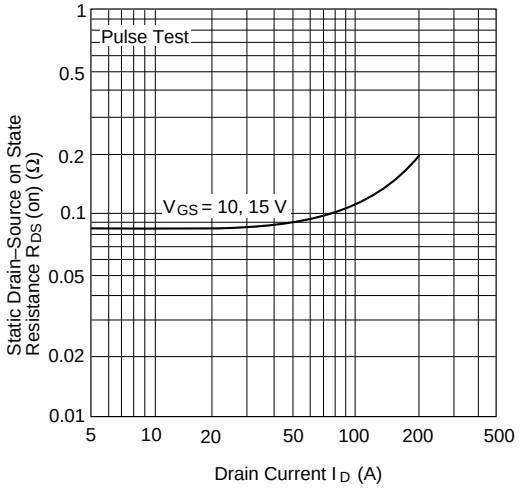
Typical Transfer Characteristics



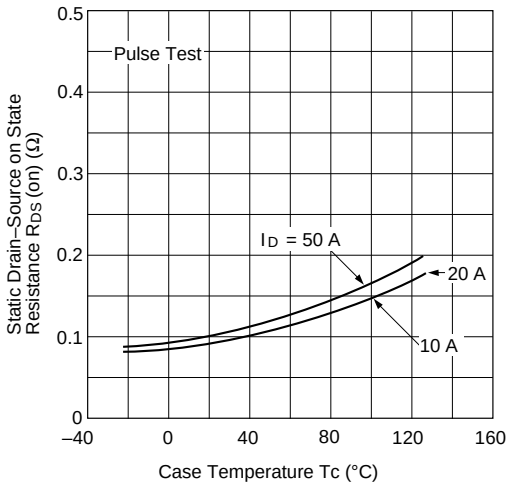
Drain to Source Saturation Voltage vs. Gate to Source Voltage



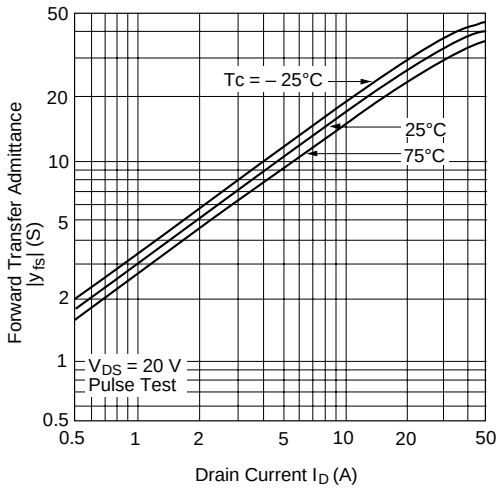
Static Drain to Source on State Resistance vs. Drain Current



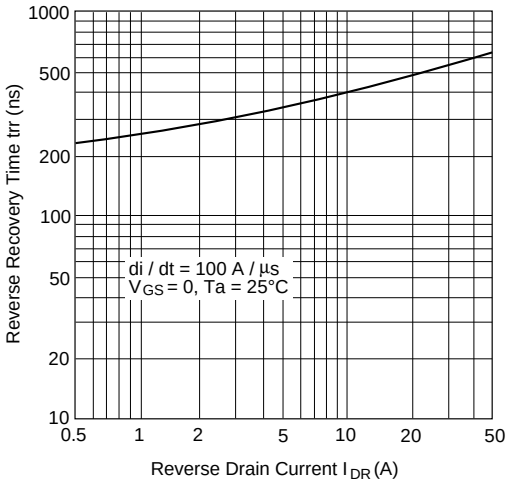
Static Drain to Source on State Resistance vs. Temperature



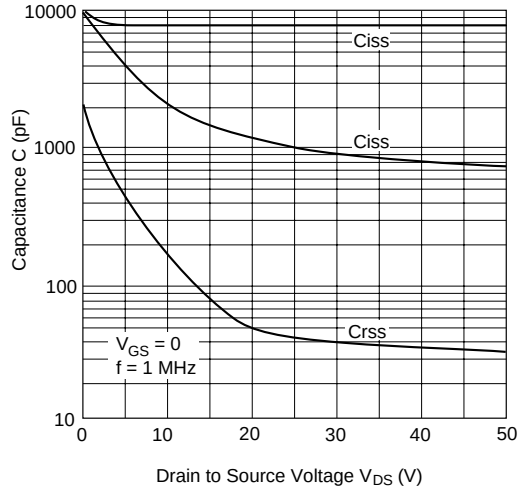
Forward Transfer Admittance vs. Drain Current



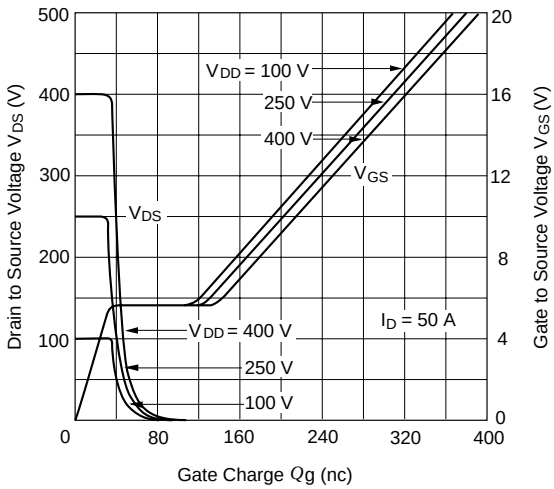
Body to Drain Diode Reverse Recovry Time



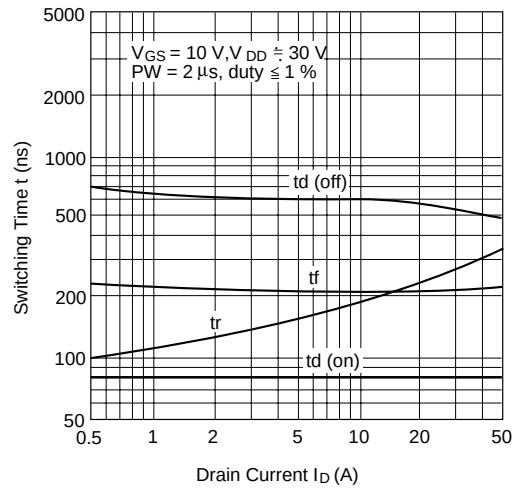
Typical Capacitance vs. Drain to Source Voltage



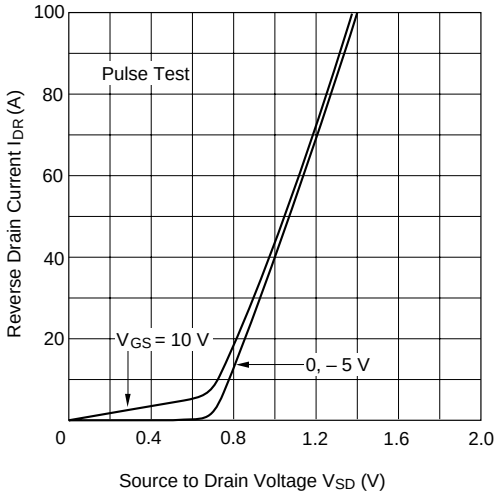
Dynamic Input Characteristics



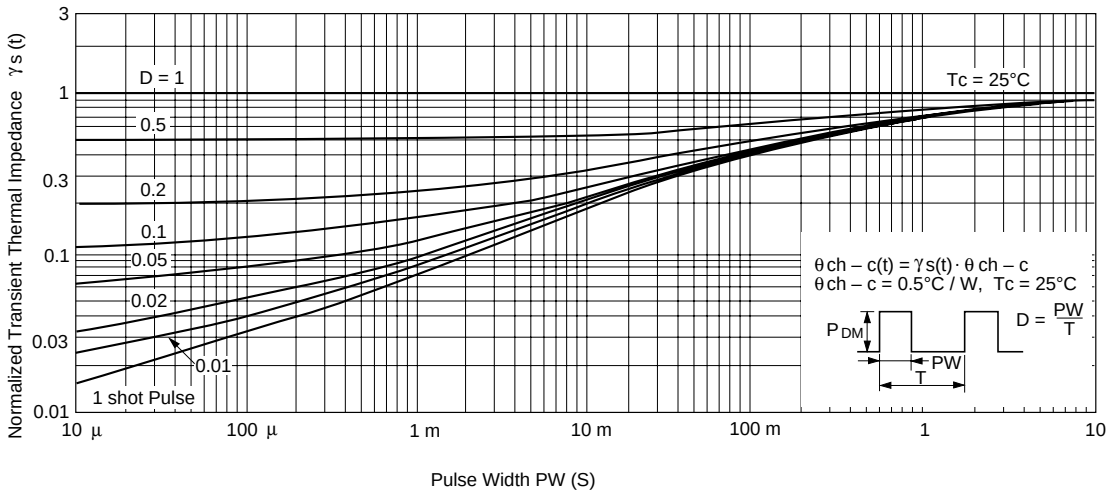
Switching Characteristics



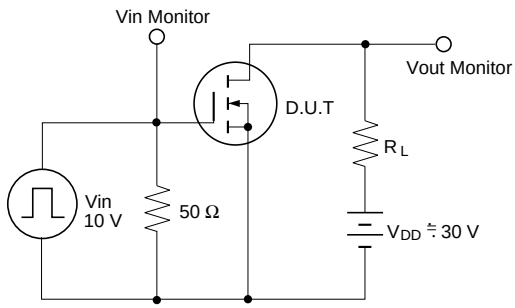
Reverse Drain Current
vs. Source Drain Voltage



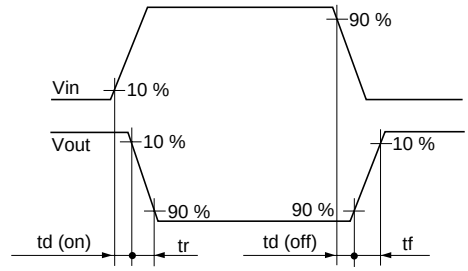
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit



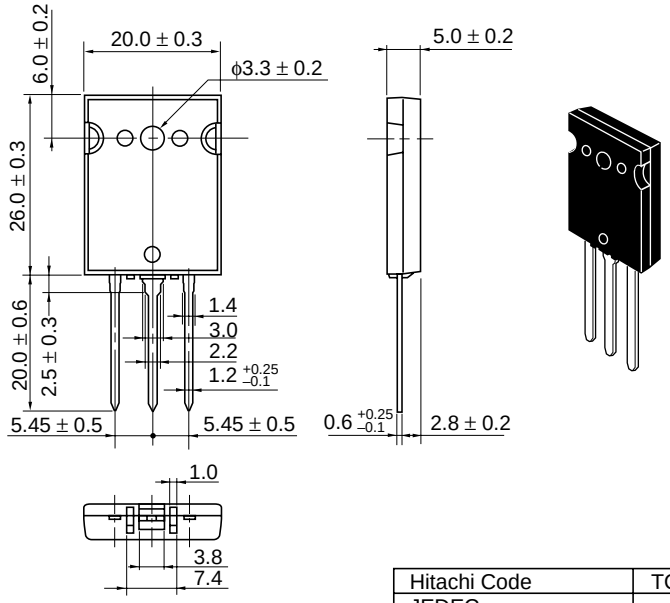
Waveforms



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-3PL
JEDEC	—
EIAJ	—
Mass (reference value)	9.9 g

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : http://semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor (America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straβe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
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